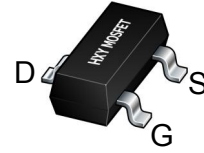




### Description

The SSM3J334R uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



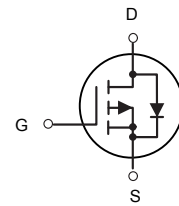
SOT-23-3L

### General Features

$V_{DS} = -30V, I_D = -4.1A$   
 $R_{DS(ON)} < 55m\Omega @ V_{GS}=10V$

### Application

- High power and current handing capability
- Lead free product is acquired
- Surface mount package
- PWM applications
- Load switch
- Power management



P-Channel MOSFET

### Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SSM3J334R	SOT-23-3L	HXY MOSFET	3000

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	-4.1	A
$I_{DM}$	Drain Current-Pulsed (Note 1)	-13	A
$P_D$	Maximum Power Dissipation	1.32	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	125	$^\circ C/W$



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.02	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A	---	42	55	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.5A	---	90	98	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.2	-1.5	-2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4.32	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	-5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-3A	---	4.8	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	24	48	Ω
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-20V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	---	5.22	7.3	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.25	1.8	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.3	3.2	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =-1A	---	18.4	37	ns
T <sub>r</sub>	Rise Time		---	11.4	21	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	39.4	79	
T <sub>f</sub>	Fall Time		---	5.2	10.4	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	---	463	650	pF
C <sub>oss</sub>	Output Capacitance		---	82	115	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	68	95	
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-3.2	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>		---	---	-13	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.



### Typical Characteristics



Fig.1 Typical Output Characteristics



Fig.2 On-Resistance vs. G-S Voltage

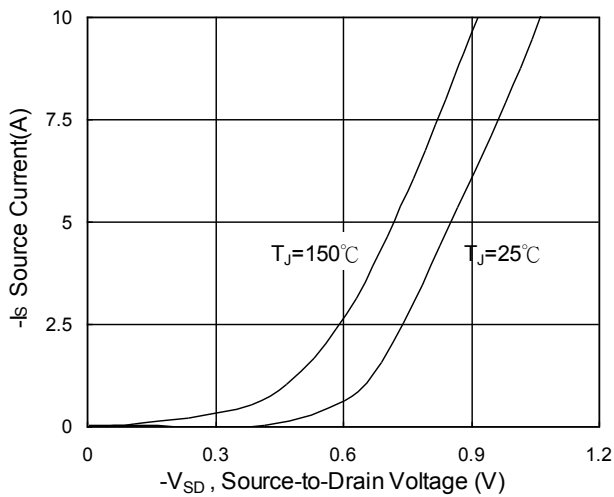


Fig.3 Source Drain Forward Characteristics



Fig.4 Gate-Charge Characteristics

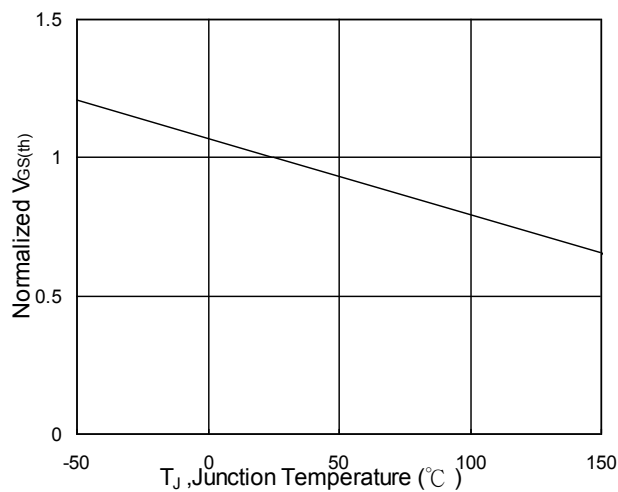


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$



Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$



Fig.7 Capacitance

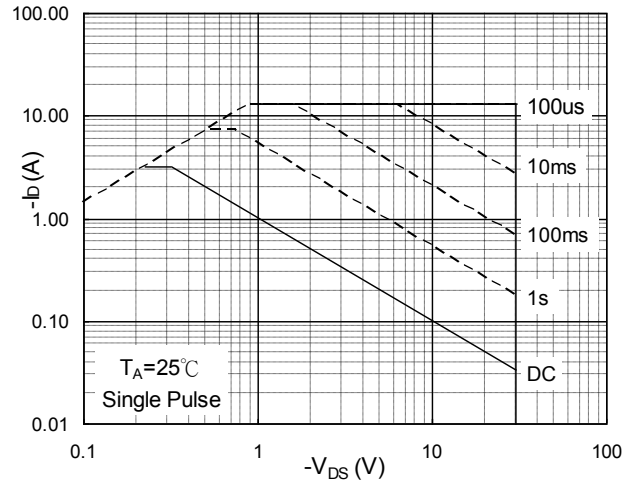


Fig.8 Safe Operating Area

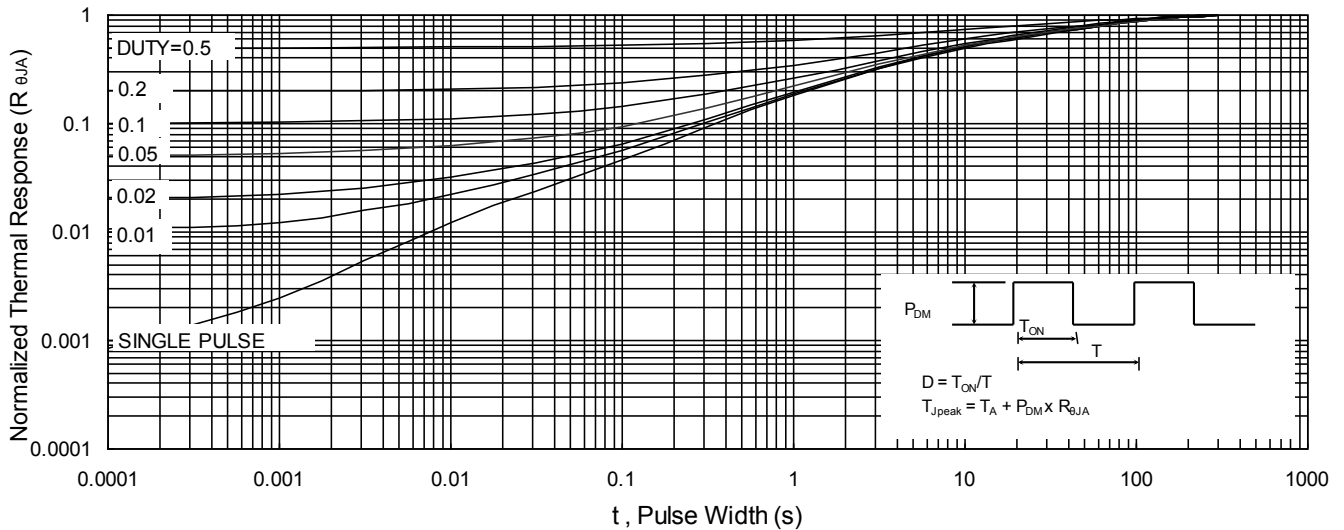


Fig.9 Normalized Maximum Transient Thermal Impedance



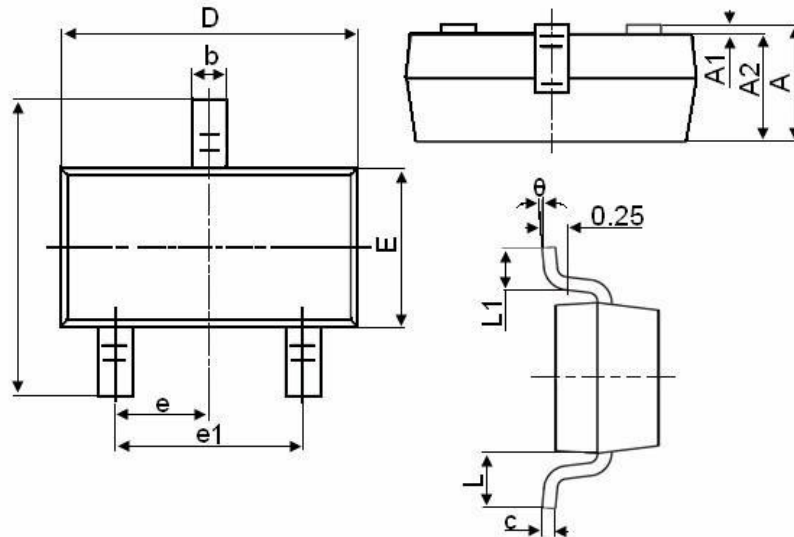
Fig.10 Switching Time Waveform



Fig.11 Gate Charge Waveform



### SOT-23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°



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